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Electrodeposition of uniform gloss photoresist pattern
involves preliminary step of chemical polishing copper surface with
benzene carboxylate deriv., gives high resolution pattern.

Patent Assignee: DAINIPPON TORYO KK (DNTO); HITACHI CHEM CO LTD (HITB);
TOKAI DENKA KOGYO KK (TOJV)

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Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
JP 7126892	A	19950516	JP 93105374	A	19930506	199528 B

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Patent Details:

Patent No	Kind	Lan Pg	Main IPC	Filing Notes
JP 7126892	A	10	C25D-013/20	

Abstract (Basic): JP 7126892 A

Electrodeposition of photoresist comprises (a) surface treatment of
substrate having Cu surface layer using a chemical polisher which
contains a benzene carboxylate deriv. of formula (I) where R = H, CH₃,
OCH₂, NO₂, SO₃H, OH, CHO, F, Br, or I, and n = 1-6; and (b) then the
electrodeposition is applied.

USE - Electrodeposition of photoresist.

ADVANTAGE - The prepd. photoresist has a uniform gloss, and
provides high resolution resist pattern.

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